

SEMICONDUCTOR

December 2013

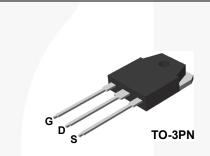
FQA13N50C_F109 N-Channel QFET[®] MOSFET 500 V, 13.5 A, 480 mΩ

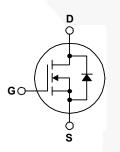
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.

Features

- 13.5 A, 500 V, $R_{DS(on)}$ = 480 m Ω (Max.) @ V_{GS} = 10 V, I_D = 6.75 A
- Low Gate Charge (Typ. 43 nC)
- Low Crss (Typ. 20 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA13N50C_F109	Unit
V _{DSS}	Drain-Source Voltage	500	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		13.5	A
	- Continuous (T _C = 100°C)		8.5	A
I _{DM}	Drain Current - Pulsed	(Note 1)	54	A
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	860	mJ
I _{AR}	Avalanche Current	(Note 1)	13.5	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	21.8	mJ
dv/dt	Peak Diode Recovery dv/dt (No		4.5	V/ns
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		218	W
	- Derate above 25°C	1.56	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C

Thermal Characteristics

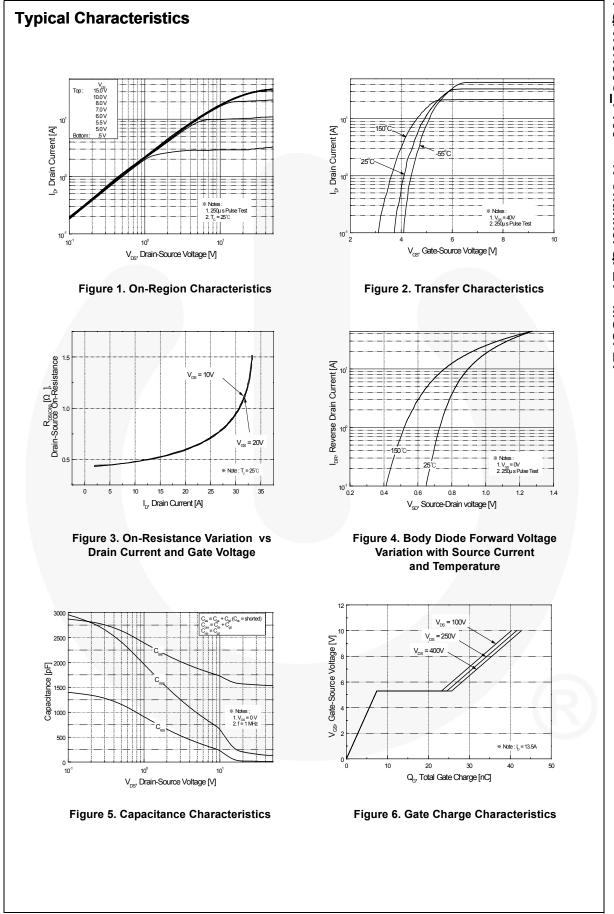
Symbol	Parameter	FQA13N50C_F109	Unit °C/W	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.58		
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

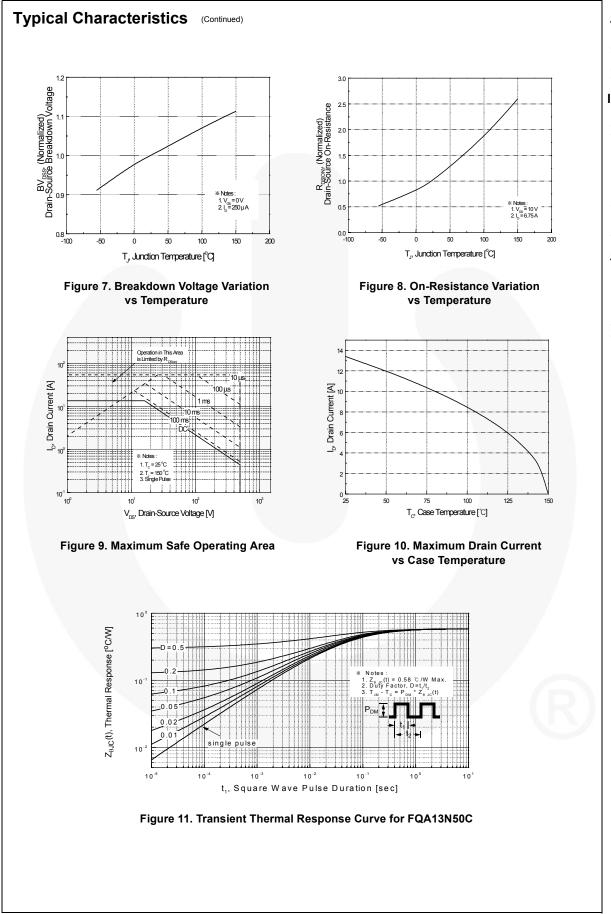
Part Number FQA13N50C_F109			Package	Packing Method	Reel	Reel Size		/idth	Quantity 30 units
			TO-3PN	Tube	N/	'A	N/A		
Electri	cal Chara	acteristics _{Tc}	= 25°C unless othe	erwise noted.					
Symbol		Parameter		Test Conditions		Min.	Тур.	Max.	Unit
Off Cha	aracteristic	s							
BV _{DSS}		e Breakdown Voltage	$V_{GS} = 0$	V _{GS} = 0 V, I _D = 250 μA					V
ΔBV _{DSS}		Voltage Temperature							
$/\Delta T_{J}$	Coefficient		$I_{\rm D} = 250$	$I_D = 250 \ \mu A$, Referenced to $25^{\circ}C$			0.5		V/°C
I _{DSS}	Zara Cata V			V _{DS} = 500 V, V _{GS} = 0 V				1	μA
	Zero Gate Voltage Drain Current		V _{DS} = 4	V _{DS} = 400 V, T _C = 125°C				10	μA
I _{GSSF}	Gate-Body I	_eakage Current, Forw	ard V _{GS} = 3	80 V, V _{DS} = 0 V				100	nA
I _{GSSR}	Gate-Body I	_eakage Current, Reve	rse V _{GS} = -	30 V, V _{DS} = 0 V			I	-100	nA
On Cha	racteristic	s							
V _{GS(th)}	Gate Thresh		V _{DS} = V	/ _{GS} , I _D = 250 μA		2.0		4.0	V
R _{DS(on)}	Static Drain- On-Resistar	Source		0 V, I _D = 6.75 A			0.39	0.48	Ω
9 _{FS}		insconductance	V _{DS} = 4	0 V, I _D = 6.75 A	-		15		S
Dynam C _{iss} C _{oss}	ic Charact Input Capac Output Capa	itance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz			1580 180	2055 235	pF pF
C _{rss}		Insfer Capacitance	1 1.01	1112			20	25	pF
	ing Charac	-							
t _{d(on)}	Turn-On De	lay Time	Vpp = 2	V _{DD} = 250 V, I _D = 13.5 A,			25	60	ns
t _r	Turn-On Ris	e Time	$R_{\rm G} = 25$	-			100	210	ns
t _{d(off)}	Turn-Off De	lay Time	Ŭ				130	270	ns
t _f	Turn-Off Fal	I Time		(Note 4)		100	210	ns
Qg	Total Gate C	ů.		00 V, I _D = 13.5 A,			43	56	nC
Q _{gs}	Gate-Source	e Charge	V _{GS} = 1	0 V			7.5		nC
Q _{gd}	Gate-Drain	Charge		(Note 4)		18.5		nC
Drain-S	ource Dio	de Characteristic	s and Maxi	imum Ratinos					
I _S	Maximum Continuous Drain-Source Diode Forward Current					13	Α		
I _{SM}	Maximum P	ulsed Drain-Source Die	de Forward C	urrent				52	А
V _{SD}	Drain-Sourc	e Diode Forward Volta	ge V _{GS} = C) V, I _S = 13.5 A				1.4	V
	Boyoraa Bo	covery Time	$V_{ab} = 0$) V, I _S = 13.5 A,			410		ns
t _{rr}	Reverse Re		v _{GS} – u	, v, ig – 15.5 A,			410		

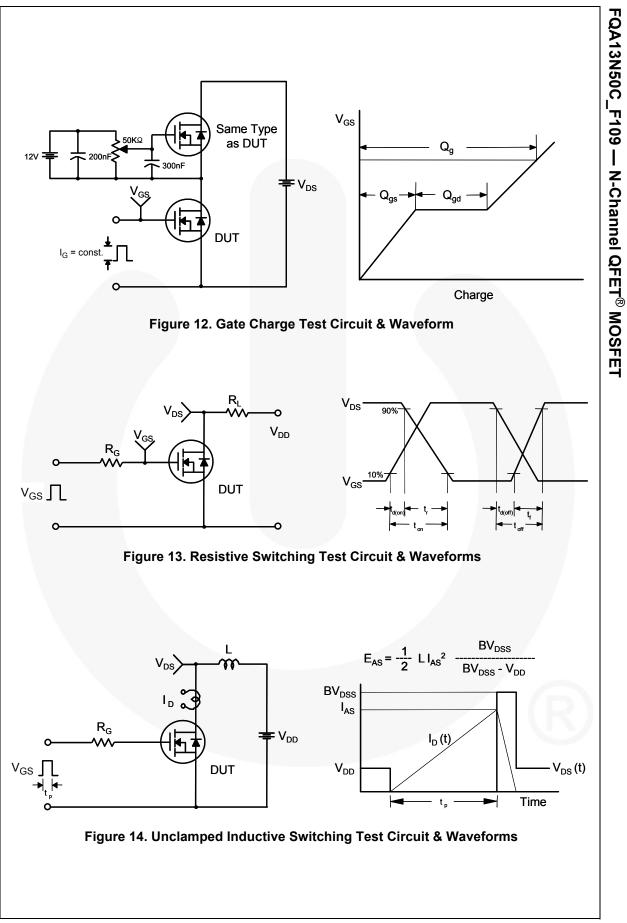
Notes:

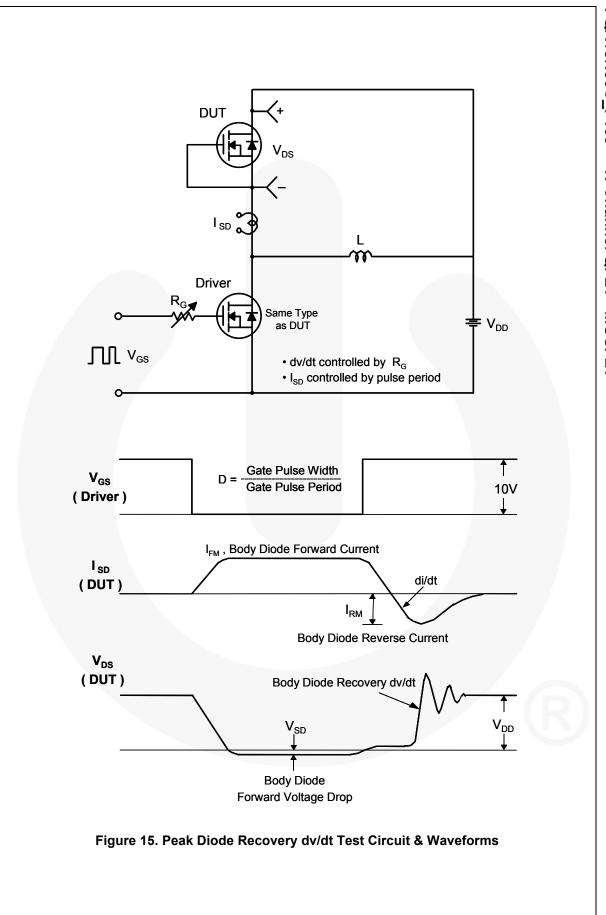
1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 5.6 mH, I_{AS} = 13.5 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} ≤ 13.5 A, di/dt ≤ 200 A/µs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C. 4. Essentially independent of operating temperature

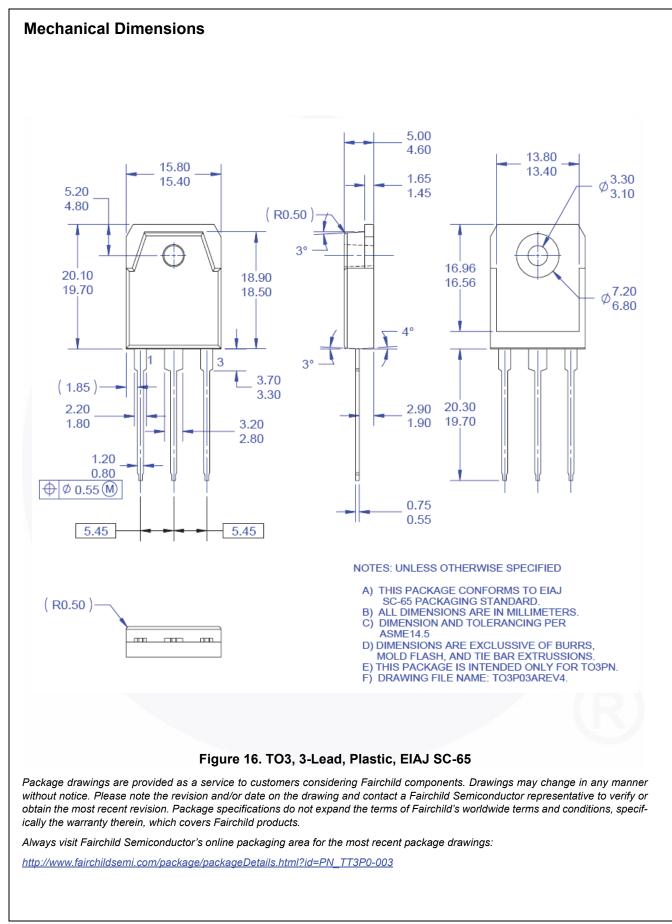
FQA13N50C_F109 — N-Channel QFET[®] MOSFET













N-Channel QFET[®] MOSFE

No Identification Needed

Obsolete

Full Production

Not In Production

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Datasheet contains specifications on a product that is discontinued by Fairchild

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